

产品规格书

Specification of Products

产品名称：MOSFET模块

产品型号：1000A100V-K2B

浙江世菱电力电子有限公司

ZHEJIANG SHILING POWER ELECTRON CO.,LTD.

厂址：浙江省 缙云县 五东工业区

电话：（0578）3012571 3615078

传真：（0578）3611180

邮编：321400

E-mail:smrshiling01@163.com

Http://www.smrshiling.com

拟制	审核	核准
金明辉	曹剑龙	宗瑞

SEMICONDUCTOR

MOSFET

Molding Type Module

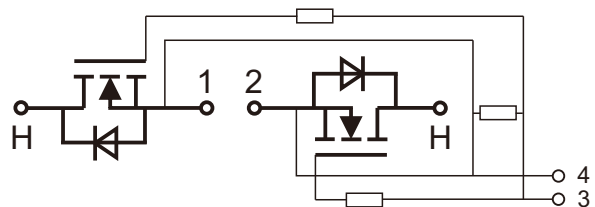
100V/1000A 2 in one-package

General Description

SHILINGPOWER MOSFET Power Module provides very low $R_{DS(on)}$ as well as optimized intrinsic diode. It s designed for the applications such SMPS and DC drives.

Features

- Low $R_{DS(on)}$
- Optimized intrinsic reverse diode
- Low inductance case avoid oscillations
- Kelvin source terminals for easy drive
- Isolated copper baseplate using DBC technology



Equivalent Circuit Schematic

Typical Applications

- Main and auxiliary AC drives of electric vehicles
- DC servo and robot drives
- Battery vehicles
- UPS equipment
- Plasma cutting

Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Description		Units
V_{DSS}	Drain-Source Voltage	100	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current @ $T_C=25^{\circ}\text{C}$ @ $T_C=80^{\circ}\text{C}$	1000 620	A
I_F	Diode Forward Current	1000	A
P_D	Maximum Power Dissipation @ $T_J=175^{\circ}\text{C}$	1630	W
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{pp}	Operating Junction Temperature	- 40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	- 40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	2500	V
Mounting Torque	Power Terminal Screw:M6 Mounting Screw:M6	3.5to 4.0 3.0 to 5.0	N.m

Electrical Characteristics of MOSFET $T_C=25^{\circ}\text{C}$ unless otherwise noted

Off Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$T_J=25^{\circ}\text{C}$	100			V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=V_{DSS}$, $V_{GS}=0\text{V}$, $T_J=25^{\circ}\text{C}$			1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20\text{V}$, $T_J=25^{\circ}\text{C}$			± 100	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{GS(th)}$	Gate-Source Threshold Voltage	$I_D=250\mu\text{A}$, $V_{DS}=V_{GS}$, $T_J=25^{\circ}\text{C}$	3.0		5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$I_D=2\text{A}$, $V_{GS}=10\text{V}$, $T_J=25^{\circ}\text{C}$			0.8	m Ω
g_{fs}	Forward Transconductance	$V_{DS}=50\text{V}$, $I_D=600\text{A}$	408			S

Switching Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
R_{Gint}	Internal Gate Resistance			0.95		Ω
$t_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V, I_D=600A,$ $R_G=0.26\Omega, V_{GS}=10V,$ $T_j=25^\circ C$		25		ns
t_r	Rise Time			110		ns
$t_{d(off)}$	Turn-Off Delay Time			68		ns
t_f	Fall Time			78		ns
Q_g	Total Gate Charge	$I_D=600A, V_{DS}=80V,$ $V_{GS}=10V$		2040		nC
Q_{gs}	Gate-Source Charge			506		nC
Q_{gd}	Gate-Drain ("Miller") Charge			640		nC
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=50V,$ $f=1.0MHz$		92.2		nF
C_{oss}	Output Capacitance			6.48		nF
C_{rss}	Reverse Transfer Capacitance			3.36		nF
L_{CE}	Stray Inductance				20	nH
R_{CC+EE}	Module Lead Resistance, Terminal to Chip	$T_C=25^\circ C$		0.35		m Ω

Electrical Characteristics of Inverse Diode $T_C=25^\circ C$ unless otherwise

noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Diode Forward Voltage	$I_F=600A, V_{GS}=0V, T_j=25^\circ C$			1.30	V
t_{rr}	Diode Reverse Recovery Time	$V_R=85V, I_F=600A,$ $di/dt=1000A/\mu s, T_j=25^\circ C$		45		ns
Q_{rr}	Diode Reverse Recovery Charge			0.98		μC

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case (per MOSFET)		0.092	K/W
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)	0.035		K/W
Weight	Weight of Module	115		g

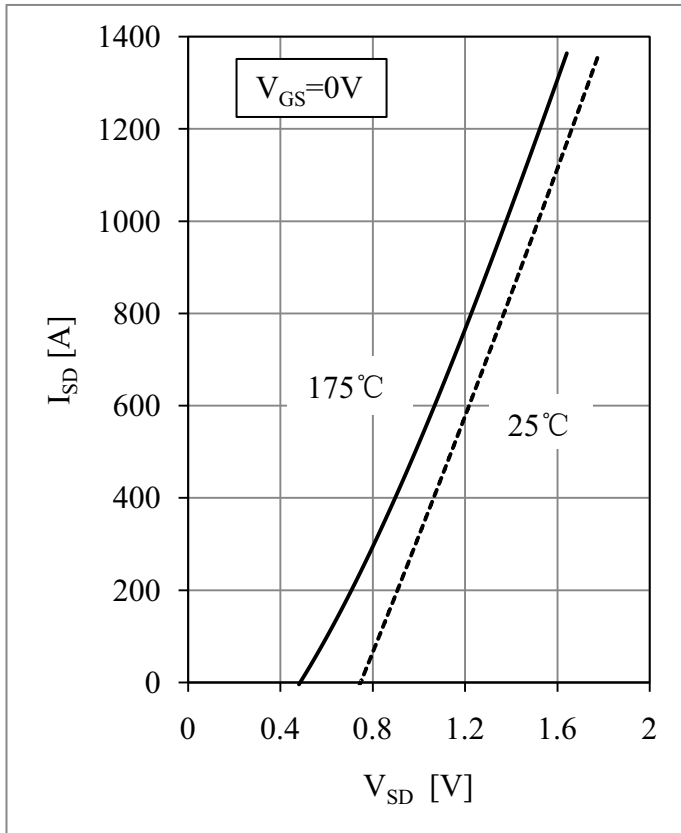


Fig 5. Inverse Diode Output Characteristic

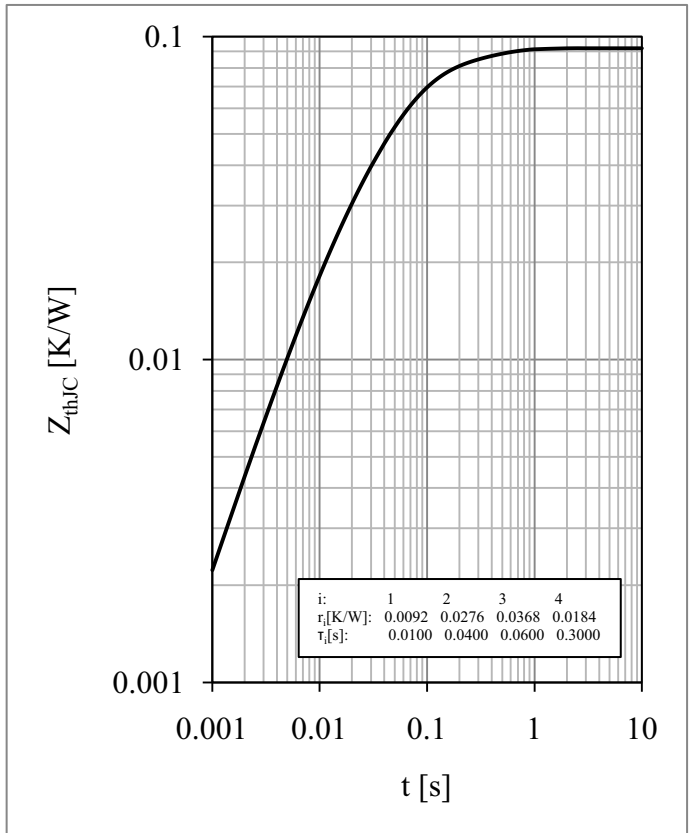


Fig 6. Transient Thermal Impedance

Package Dimension

